

RT3A66M-T150

Dual Transistor
For Differential Amplify Application
Silicon PNP Epitaxial Type

AEC-Q101 Compliance

DESCRIPTION

RT3A66M is a silicon PNP epitaxial type dual transistor.
It is designed for differential amplify application.

FEATURE

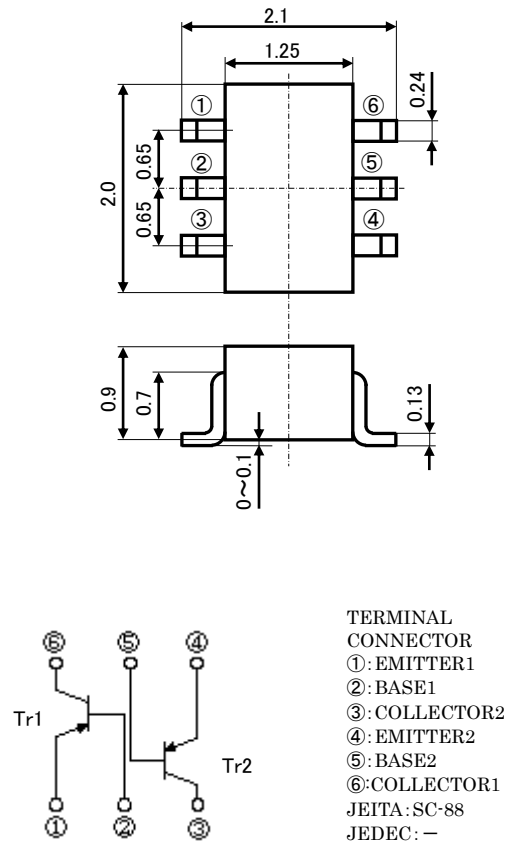
- High V_{CEO} $V_{CEO} = -150V$
- Good two elements characteristics
 $hFE1/hFE2 = 1.0$ typ
 $|V_{BE1} - V_{BE2}| = 0mV$ typ

APPLICATION

For differential amplify application.

OUTLINE DRAWING

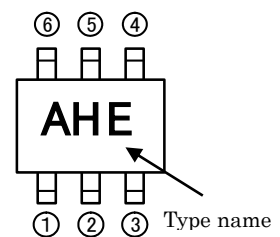
Unit: mm



MAXIMUM RATING ($T_a = 25^\circ C$) ($Tr1$, $Tr2$)

SYMBOL	PARAMETER	RATING	UNIT
VCBO	Collector to Base voltage	-160	V
VEBO	Emitter to Base voltage	-5	V
VCEO	Collector to Emitter voltage	-150	V
ICM	Peak collector current	-200	mA
IC	Collector current	-100	mA
PT	Total dissipation	200	mW
T_j	Junction temperature	+150	$^\circ C$
T_{stg}	Storage temperature	-55 ~ +150	$^\circ C$

MARKING



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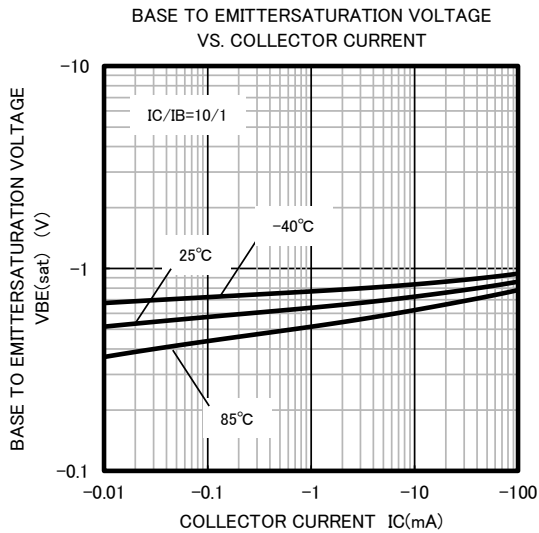
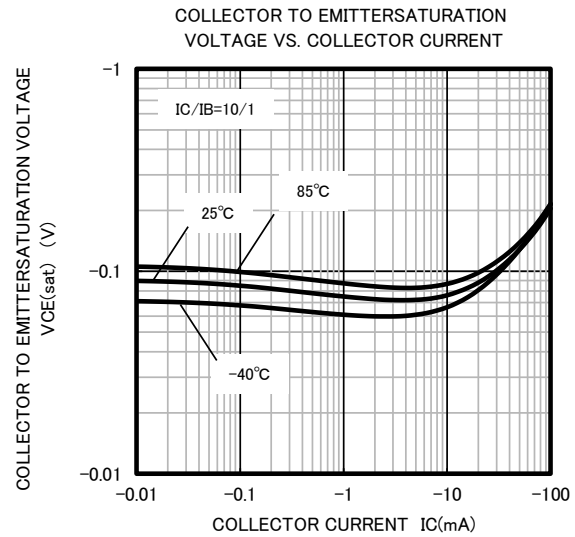
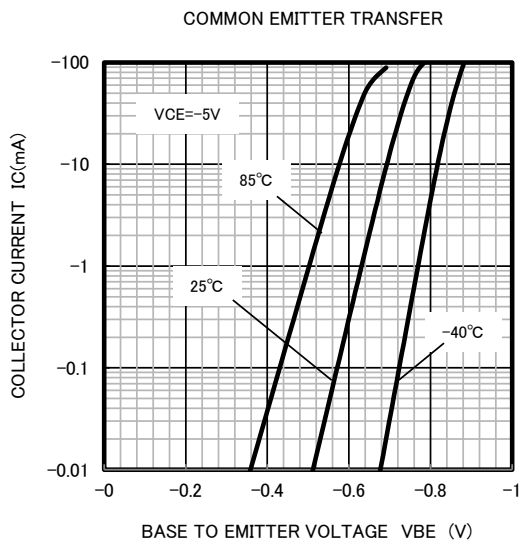
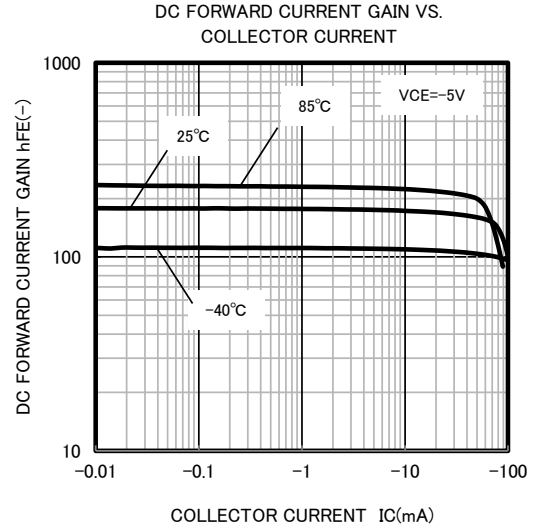
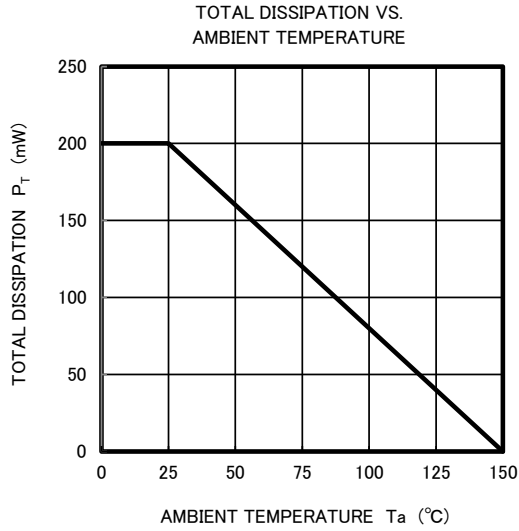
ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1, Tr2.)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V(BR)CBO	C to B breakdown voltage	IC=-100μA, IE=0mA	-160	-	-	V
V(BR)EBO	E to B breakdown voltage	IE=-10μA, IC=0mA	-5	-	-	V
V(BR)CEO	C to E breakdown voltage	IC=-1mA, RBE=∞	-150	-	-	V
ICBO	Collector cut off current	VCE=-120V, IE=0mA	-	-	-100	nA
IEBO	Emitter cut off current	VEB=-3V, IC=0mA	-	-	-100	nA
hFE1	DC forward current gain1	VCE=-5V, IC=-1mA	45	-	-	-
hFE2	DC forward current gain2	VCE=-5V, IC=-10mA	90	-	270	-
hFE3	DC forward current gain3	VCE=-5V, IC=-50mA	45	-	-	-
VCE(sat)1	C to E saturation voltage1	IC=-10mA, IB=-1mA	-	-	-0.2	V
VCE(sat)2	C to E saturation voltage2	IC=-50mA, IB=-5mA	-	-	-0.5	V
VBE(sat)1	B to E saturation voltage1	IC=-10mA, IB=-1mA	-	-	-1.0	V
VBE(sat)2	B to E saturation voltage2	IC=-50mA, IB=-5mA	-	-	-1.0	V
$\frac{ V_{BE1}-V_{BE2} }{(\times V_{BE1:Tr1}, V_{BE2:Tr2})}$	B-E voltage differential	VCE=-5V, IC=-1mA	-	0	10	mV
$\frac{h_{FE1}/h_{FE2}}{(\times h_{FE1:Tr1}, h_{FE2:Tr2})}$	DC forward current gain ratio	VCE=-5V, IC=-1mA	0.9	1.0	1.1	-
VBE(on)	B to E on voltage	VCE=-5V, IC=-10mA	-	-	-0.77	V
fT	Gain bandwidth product	VCE=-10V, IE=10mA	100	-	300	MHz
Cob	Collector output capacitance	VCE=-10V, IE=0mA, f=1MHz	-	2.8	6	pF

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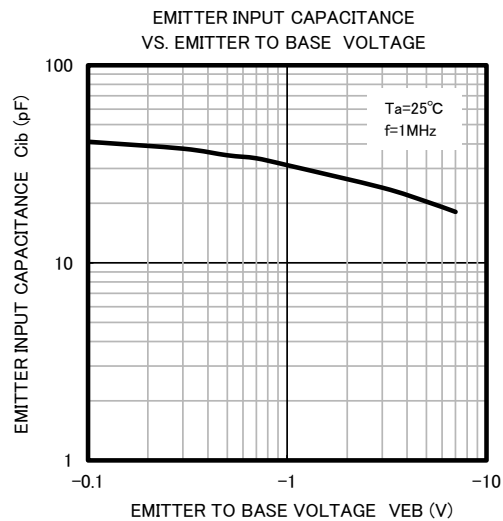
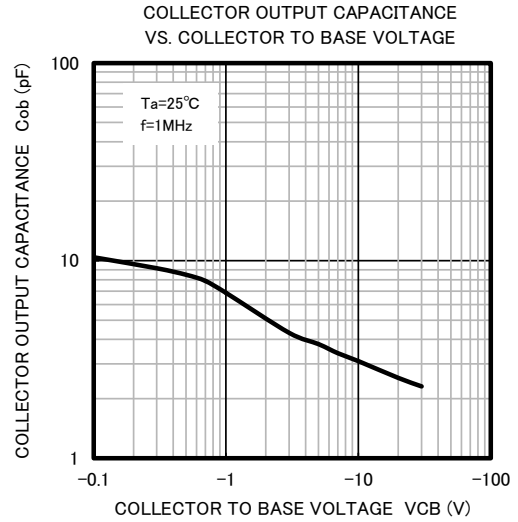
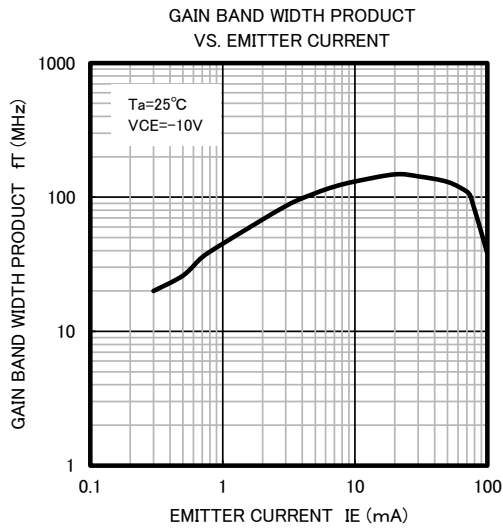
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TYPICAL CHARACTERISTICS (Tr1,Tr2.)



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